19. (Amended) The method according to claim 13, wherein:

the solid glass layer is applied both on the front side of the semiconductor wafer and on the back side of the semiconductor wafer, a doping type of the dopant on the back side being the same compared to the doping type of the dopant on the front side.

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20. (Amended) The method according to claim 13, wherein:

the solid glass layer is applied both on the front side of the semiconductor wafer and on the back side of the semiconductor wafer, a doping type of the dopant on the back side being opposite compared to the doping type of the dopant on the front side.

23. (Amended) The method according to claim 21, wherein:

the dopant constituent of the solid glass layer on the front side of the semiconductor wafer is different from the dopant constituent of the solid glass layer on the back side of the semiconductor wafer.

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24. (Amended) The method according to claim 22, wherein:

the dopant constituent of the solid glass layer on the front side of the semiconductor wafer is different from the dopant constituent of the solid glass layer on the back side of the semiconductor wafer.

Please add without prejudice new claims 29 and 30 as follows:

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29. (New) The method according to claim 13, wherein the high temperature is at least 1200 degrees centigrade.

30. (New) The method according to claim 29, wherein the high temperature is between 1200 and 1280 degrees centigrade.